

Description:

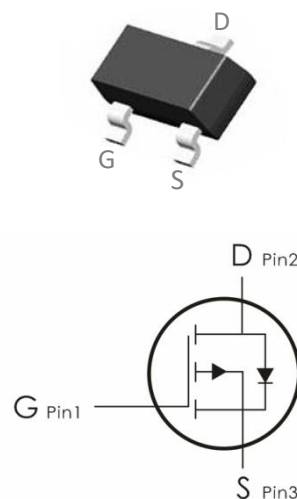
This P-Channel MOSFET uses advanced trench technology and

design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-20V, I_D=-3A, R_{DS(on)} < 55m\Omega @ V_{GS}=-4.5V$ (Typ: $43m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DO2301B	A1SHB/2301B	SOT-23	3000 pcs/Reel

Absolute Maximum Ratings: ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current- $T_A=25^\circ C$	-3	A
	Continuous Drain Current- $T_A=100^\circ C$	-2	
I_{DM}	Pulsed Drain Current ¹	-12	
P_D	Power Dissipation	1	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	$^\circ C/W$

Electrical Characteristics: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	-20	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-20V	---	---	-1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 12V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	-0.5	-0.7	-1	V
R _{DS(ON)}	Drain-Source On Resistance ²	V _{GS} =-4.5V, I _D =-3A	---	43	55	m Ω
		V _{GS} =-2.5V, I _D =-2A	---	54	70	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	---	477	---	pF
C _{oss}	Output Capacitance		---	70	---	
C _{rss}	Reverse Transfer Capacitance		---	60	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =-10V, I _D =-3A, R _{ENG} =1 Ω ,V _{GS} =-4.5V, R _L =1.2 Ω	---	11.5	---	ns
t _r	Rise Time		---	54	---	ns
t _{d(off)}	Turn-Off Delay Time		---	16.8	---	ns
t _f	Fall Time		---	10.5	---	ns
Q _g	Total Gate Charge	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-2A	---	4.3	---	nc
Q _{gs}	Gate-Source Charge		---	0.84	---	nc
Q _{gd}	Gate-Drain “Miller” Charge		---	1.15	---	nc
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage ¹	V _{GS} =0V, I _{SD} =-3A	---	---	-1.2	V
I _S	Continuous Drain Curren ³	V _D =V _G =0V	---	---	-3	A
I _{SM}	Pulsed Drain Current		---	---	-12	A

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

Typical Characteristics: ($T_A=25^\circ C$ unless otherwise noted)

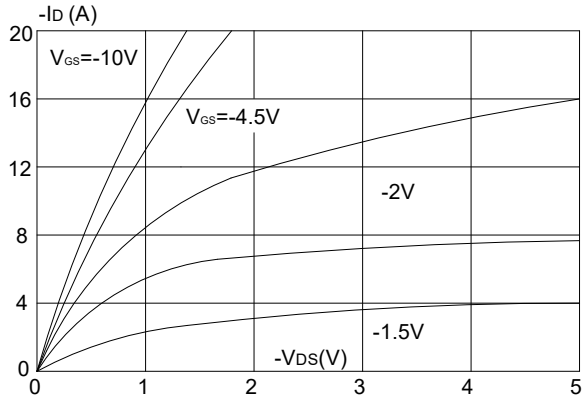


Figure 1: Output Characteristics

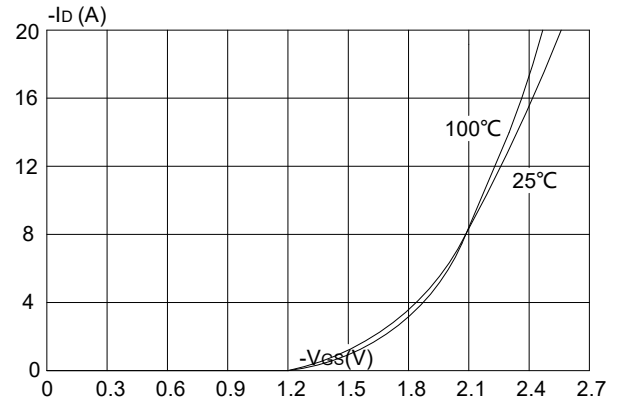


Figure 2: Typical Transfer Characteristics

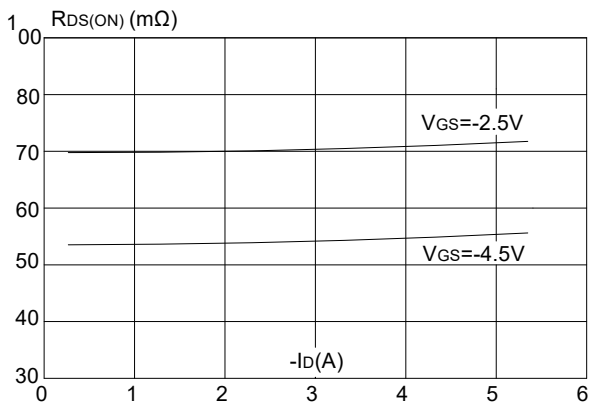


Figure 3: On-resistance vs. Drain Current

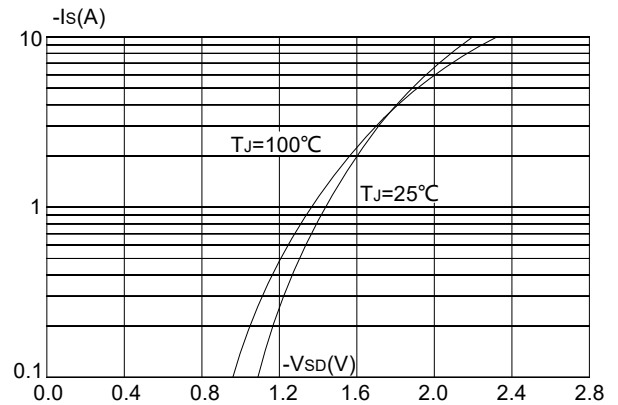


Figure 4: Body Diode Characteristics

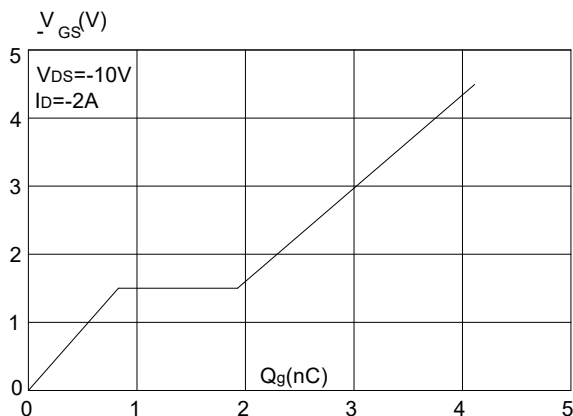


Figure 5: Gate Charge Characteristics

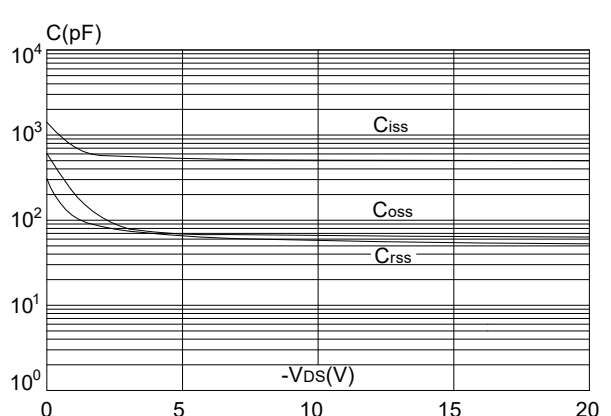


Figure 6: Capacitance Characteristics

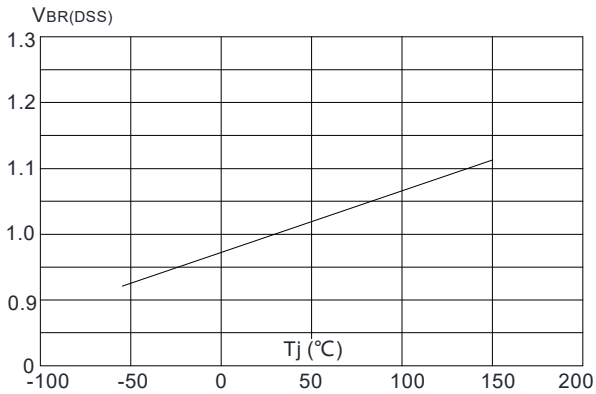


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

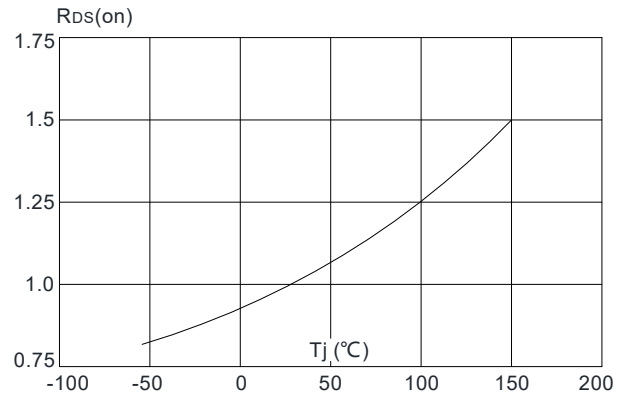


Figure 8: Normalized on Resistance vs. Junction Temperature

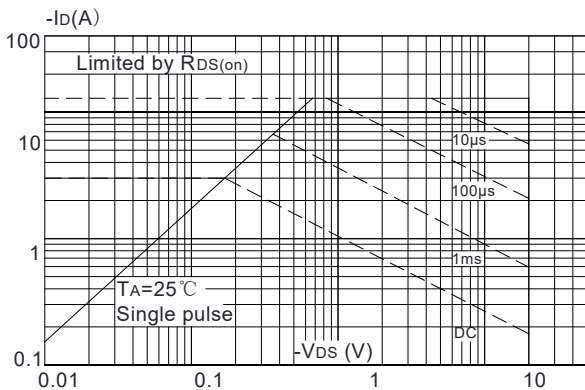


Figure 9: Maximum Safe Operating Area

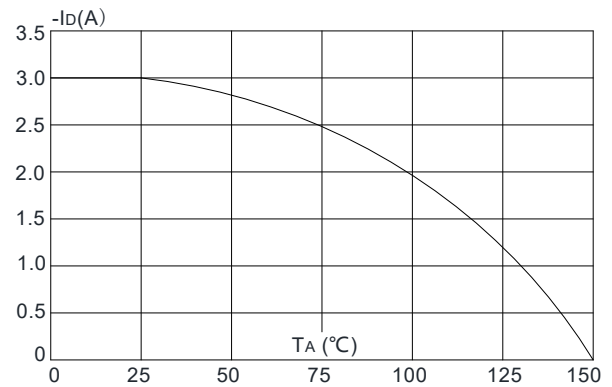


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

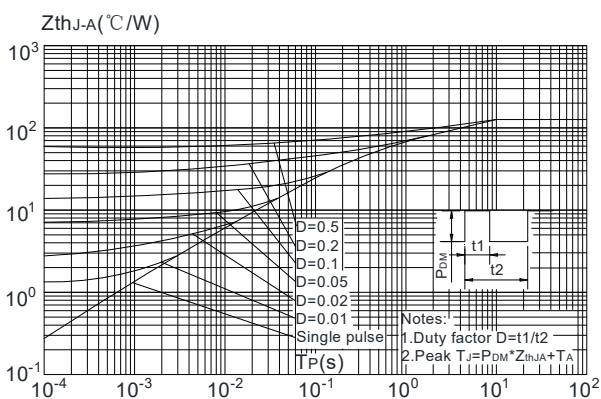
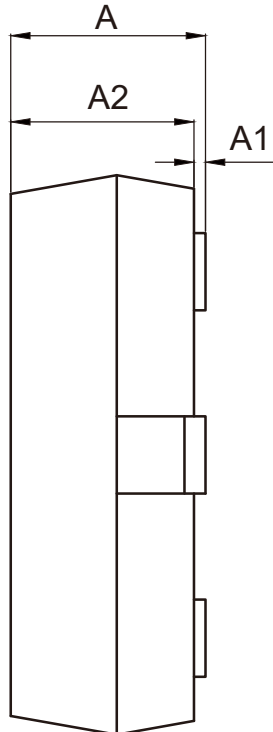
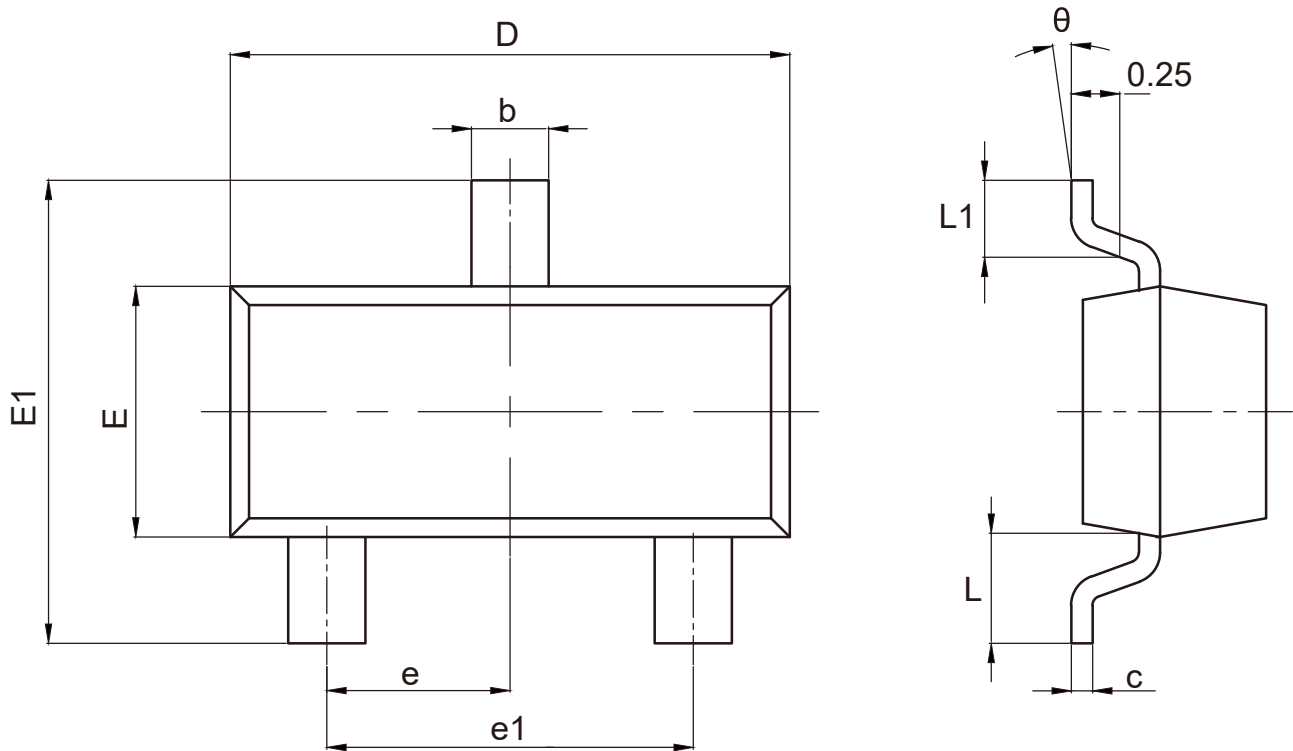


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

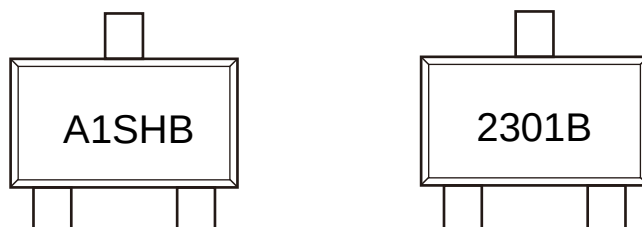
SOT-23 Package Outline Data



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER			
SYMBOL	MIN	NOM	MAX
A	0.900	--	1.150
A1	0.000	--	0.100
A2	0.900	--	1.050
c	0.100	--	0.200
b	0.300	0.400	0.500
D	2.800	2.900	3.000
E	1.200	--	1.400
E1	2.250	--	2.550
e	0.950TYP		
e1	1.800	1.900	2.000
L	0.550REF		
L1	0.300	0.400	0.500
θ	0°	--	8°

Unit:mm

Marking Information:



Previous Version

Version	Date	Subjects (major changes since last revision)
2.1	2026-02-02	Release of final version

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